WELCOME

We are pleased to welcome you to Munich for the 11th International Conference on Solid-State Sensors and Actuators. We are meeting in Europe for the first time in the new millennium and on the twentieth anniversary year of the first meeting. The conference began in Boston in 1981, followed by meetings every other year in Delft, Philadelphia, Tokyo, Montreux, San Francisco, Yokohama, Stockholm, Chicago, Sendai, and now Munich. This series of meetings, the premier conference in its field, has since its beginning been the leading forum for reporting the latest research and developments in sensors, microactuators, MEMS and microsystems. These past conferences have established a very high standard of excellence that have guided the planning for this conference. As in previous years when it was held in Europe, the conference is taking place in conjunction with the Eurosensors Conference, the most important European conference on solid-state transducers.

The technical program of the conference consists of four days of formal presentations including an opening Plenary Session, twelve invited papers interspersed throughout the technical sessions, nearly 200 contributed oral papers in four parallel sessions, and two poster sessions featuring over 200 poster papers. In recognition of the 20th anniversary of the conference, Richard S. Muller of UC Berkeley will be giving a special plenary address entitled “MEMS-The View Back ... and the Vistas Ahead”.

The Digest of Technical Papers consists of two volumes and contains all oral and poster papers in four-page format. It is also available on CD-ROM. The Digest will be available for purchase after the conference through Springer Verlag Berlin Heidelberg New York, www.springer.de

As in previous meetings an exciting social program has been planned. A Welcome Reception on Sunday evening and a Monday Evening Reception at the world-famous Deutsches Museum will provide ample opportunity to interact informally while enjoying the historical setting.

On Wednesday evening the Conference Dinner will be held at the famous Löwenbräu Keller, featuring Bavarian music and special entertainment. The Spouse and Guest Program includes a City Sightseeing Tour, an exciting series of cultural events, and a post-conference tour to the King Ludwig II Musical and the enchanting Neuschwanstein castle.

On behalf of the International Steering Committee on Solid-State Sensors and Actuators, and the Eurosensors International Steering Committee, we would like to thank the 53 members of the three Regional Technical Program Committees headed by Hermann Sandmaier (Europe), Khalil Najafi (North America), and Susumu Sugiyama (Asia) for their excellent work in reviewing more than 850 submitted abstracts from 43 countries.

We also wish to express our sincere thanks to the members of the Executive Program Committee, including the Regional Program Chairmen and five Topic Specialists (M. Koudelka-Hep, R. Popovic, A. van den Berg, G. Wachtuta, and R. Wolfenbuttel) for the outstanding job they have done in finalizing the Technical Program. The members of the Local Organizing Committee, headed by Karl Kühl, also deserve much recognition for their efforts and services contributing to the conference.

We would also like to take this opportunity to thank all of the many authors who submitted their latest work to this conference. Sincere appreciation is also given to the plenary and other invited speakers.

We are particularly grateful to our sponsors and exhibitors for their financial contributions.

Finally we would like to personally thank you for attending the conference. The outstanding program of this meeting is designed to keep you up-to-date on the most recent advances in sensors, microactuators, MEMS and microsystems. We hope you will find the meeting exciting, inspiring, and enjoyable.

Ernst Obermeier
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Helmut Seidel
Technical Program Chairman
Conference Site:

Gasteig Cultural, Educational and Conference Center, Munich, Germany

At the program committee meeting for TRANSUDERS '01 / EUROSENSORS XV

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Khalil Najafi, North American Chairman
Herman Sandmaier, European Chairman

Seated (left to right)
Susumu Sugiyama, Asian Chairman
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<td>3A3.08P</td>
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